

# **Excellent Integrated System Limited**

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Fairchild Semiconductor PN3643

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**PN3643** 

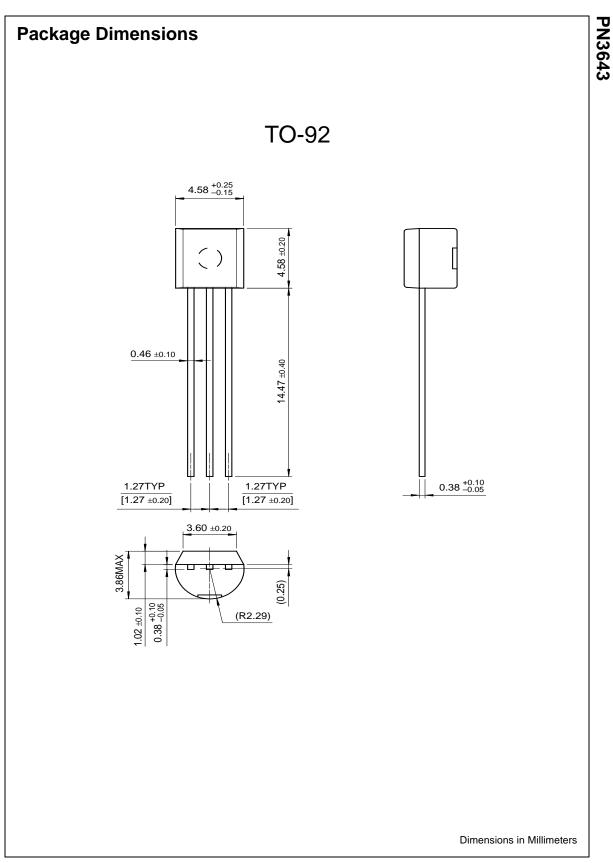
This devic	neral Purpose Amplifier e is designed for use as general purpose equiring collector currents to 300mA.	e amplifiers and			
			ТО	-92	
bsolut	e Maximum Ratings* T <sub>A</sub> =25		Emitter 2. Base		ctor
Symbo	I Param	eter	Value		Units
CEO	Collector-Emitter Voltage		30		V
сво	Collector-Base Voltage		60		V
ево	Emitter-Base Voltage		5.0		V
2	Collector Current - Con	tinuous	500		mA
J, T <sub>STG</sub>	Operating and Storage Junction re limiting values above which the serviceability of an		- 55 ~ 150		°C
	Parameter	nless otherwise noted Test Condition	Min.	Max.	Units
Symbol Off Charac	Parameter teristics	Test Condition	Min.	Max.	
Symbol Off Charac / <sub>(BR)CEO</sub>	Parameter teristics Collector-Emitter Breakdown Voltage *	Test Condition $I_C = 10$ mA, $I_B = 0$	30	Max.	V
Symbol Off Charac (BR)CEO (BR)CBO	Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0           I <sub>C</sub> = 10 $\mu$ A, I <sub>E</sub> = 0	30 60	Max.	V V
Symbol Off Charac (BR)CEO (BR)CBO (BR)EBO	Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0           I <sub>C</sub> = 10 $\mu$ A, I <sub>E</sub> = 0           I <sub>E</sub> = 10 $\mu$ A, I <sub>C</sub> = 0	30		V V V
Symbol Off Charac (BR)CEO (BR)CBO (BR)EBO	Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0           I <sub>C</sub> = 10 $\mu$ A, I <sub>E</sub> = 0	30 60	<b>Max.</b>	V V
Symbol Off Charac / <sub>(BR)CEO</sub>	Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current	$\begin{tabular}{ c c c c c } \hline Test Condition \\ \hline I_C = 10mA, I_B = 0 \\ \hline I_C = 10\muA, I_E = 0 \\ \hline I_E = 10\muA, I_C = 0 \\ \hline V_{CB} = 50V, I_E = 0 \\ \hline V_{CB} = 50V, I_E = 0, T_A = 65^\circ C \\ \hline \end{tabular}$	30 60	50	V V V nA
Symbol Off Charac (BR)CEO (BR)CBO (BR)EBO CES On Charac	Parameter teristics Collector-Emitter Breakdown Voltage * Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cut-off Current teristics DC Current Gain	$\begin{tabular}{ c c c c c } \hline Test Condition \\ \hline I_C = 10mA, I_B = 0 \\ \hline I_C = 10\muA, I_E = 0 \\ \hline I_E = 10\muA, I_C = 0 \\ \hline V_{CB} = 50V, I_E = 0 \\ \hline V_{CB} = 50V, I_E = 0, T_A = 65^\circ C \\ \hline \hline V_{CE} = 10V, I_C = 150mA \\ \hline V_{CE} = 10V, I_C = 500mA \\ \hline \end{tabular}$	30 60	50 1.0 300	V V V nA μA
Symbol Off Charace (BR)CEO (BR)CBO (BR)EBO CES On Charace PFE (CE(sat)	Parameter         teristics         Collector-Emitter Breakdown Voltage *         Collector-Base Breakdown Voltage         Emitter-Base Breakdown Voltage         Collector Cut-off Current         teristics         DC Current Gain         Collector-Emitter Saturation Voltage	Test Condition $I_C = 10mA, I_B = 0$ $I_C = 10\muA, I_E = 0$ $I_E = 10\muA, I_C = 0$ $V_{CB} = 50V, I_E = 0$ $V_{CB} = 50V, I_E = 0, T_A = 65^{\circ}C$ $V_{CE} = 10V, I_C = 150mA$	30 60 5.0 100	50 1.0	V V V nA
Symbol Off Charace (BR)CEO (BR)CBO (BR)EBO CES On Charace PFE (CE(sat) Small Sign	Parameter         teristics         Collector-Emitter Breakdown Voltage *         Collector-Base Breakdown Voltage         Emitter-Base Breakdown Voltage         Collector Cut-off Current         teristics         DC Current Gain         Collector-Emitter Saturation Voltage	$\begin{tabular}{ c c c c }\hline \hline Test Condition \\ \hline I_C = 10mA, I_B = 0 \\ \hline I_C = 10\muA, I_E = 0 \\ \hline I_E = 10\muA, I_C = 0 \\ \hline V_{CB} = 50V, I_E = 0 \\ \hline V_{CB} = 50V, I_E = 0, T_A = 65^\circ C \\ \hline \hline V_{CE} = 10V, I_C = 150mA \\ \hline V_{CE} = 10V, I_C = 500mA \\ \hline I_C = 150mA, I_B = 15mA \\ \hline \end{tabular}$	30 60 5.0 100	50 1.0 300 0.22	V V V nA μA
Symbol Off Charace (BR)CEO (BR)CBO (BR)EBO CES On Charace PFE (CE(sat)	Parameter         teristics         Collector-Emitter Breakdown Voltage *         Collector-Base Breakdown Voltage         Emitter-Base Breakdown Voltage         Collector Cut-off Current         teristics         DC Current Gain         Collector-Emitter Saturation Voltage	Test Condition $I_C = 10mA$ , $I_B = 0$ $I_C = 10\muA$ , $I_E = 0$ $I_E = 10\muA$ , $I_C = 0$ $V_{CB} = 50V$ , $I_E = 0$ $V_{CB} = 50V$ , $I_E = 0$ , $T_A = 65^{\circ}C$ $V_{CE} = 10V$ , $I_C = 150mA$ $V_{CE} = 10V$ , $I_C = 500mA$ $I_C = 150mA$ , $I_B = 15mA$ $V_{CB} = 10V$ , $f = 140KHz$ $V_{CE} = 15V$ , $f = 30MHz$	30 60 5.0 100	50 1.0 300	V V V nA μA
Symbol Off Charace (BR)CEO (BR)CBO (BR)EBO CES On Charace FE (CE(Sat) Small Sign Cob	Parameter         teristics         Collector-Emitter Breakdown Voltage *         Collector-Base Breakdown Voltage         Emitter-Base Breakdown Voltage         Collector Cut-off Current         teristics         DC Current Gain         Collector-Emitter Saturation Voltage         al Characteristics         Output Capacitance	$\begin{tabular}{ c c c c }\hline \hline Test Condition \\ \hline I_C = 10mA, I_B = 0 \\ \hline I_C = 10\muA, I_E = 0 \\ \hline I_E = 10\muA, I_C = 0 \\ \hline V_{CB} = 50V, I_E = 0 \\ \hline V_{CB} = 50V, I_E = 0, T_A = 65^\circ C \\ \hline \hline \\ \hline$	30 60 5.0 100 20	50 1.0 300 0.22	V V ν ηΑ μΑ V



Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R <sub>0JC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJC</sub> R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

PN3643





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